

## Power MOSFET



N-Channel MOSFET

### FEATURES

- Ultra low gate charge
- Reduced gate drive requirement
- Enhanced 30 V  $V_{GS}$  rating
- Reduced  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$
- Extremely high frequency operation
- Repetitive avalanche rated
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS\***  
Available

### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

### DESCRIPTION

This new series of low charge power MOSFETs achieve significantly lower gate charge over conventional MOSFETs. Utilizing the new LCDMOS technology, the device improvements are achieved without added product cost, allowing for reduced gate drive requirements and total system savings. In addition, reduced switching losses and improved efficiency are achievable in a variety of high frequency applications. Frequencies of a few MHz at high current are possible using the new low charge MOSFETs.

These device improvements combined with the proven ruggedness and reliability that are characteristic of Power MOSFETs offer the designer a new standard in power transistors for switching applications.

### PRODUCT SUMMARY

$V_{DS}$ (V)	500	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10$ V	0.85
$Q_g$ max. (nC)	39	
$Q_{gs}$ (nC)	10	
$Q_{gd}$ (nC)	19	
Configuration	Single	

### ORDERING INFORMATION

Package	TO-220AB
Lead (Pb)-free	IRF840LCPbF
Lead (Pb)-free and halogen-free	IRF840LCPbF-BE3

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	$V_{DS}$	500	V
Gate-source voltage	$V_{GS}$	$\pm 30$	
Continuous drain current	$I_D$	$T_C = 25^\circ\text{C}$	8.0
		$T_C = 100^\circ\text{C}$	5.1
Pulsed drain current <sup>a</sup>	$I_{DM}$	28	A
Linear derating factor		1.0	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	510	mJ
Repetitive avalanche current <sup>a</sup>	$I_{AR}$	8.0	A
Repetitive avalanche energy <sup>a</sup>	$E_{AR}$	13	mJ
Maximum power dissipation	$P_D$	125	W
Peak diode recovery $dV/dt$ <sup>c</sup>	$dV/dt$	3.5	V/ns
Operating junction and storage temperature range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Soldering recommendations (peak temperature) <sup>d</sup>	For 10 s	300	
Mounting torque	6-32 or M3 screw		10
			1.1
			lbf · in
			N · m

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- $V_{DD} = 50$  V, starting  $T_J = 25^\circ\text{C}$ ,  $L = 14$  mH,  $R_g = 25 \Omega$ ,  $I_{AS} = 8.0$  A (see fig. 12)
- $I_{SD} \leq 8.0$  A,  $dI/dt \leq 100$  A/ $\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150^\circ\text{C}$
- 1.6 mm from case



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	$R_{thJA}$	-	62	°C/W
Case-to-sink, flat, greased surface	$R_{thCS}$	0.50	-	
Maximum junction-to-case (drain)	$R_{thJC}$	-	1.0	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
<b>Static</b>							
Drain-source breakdown voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		500	-	-	V
$V_{DS}$ temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$ , $I_D = 1\text{ mA}$		-	0.63	-	V/°C
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$		-	-	$\pm 100$	nA
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	$\mu\text{A}$
		$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 4.8\text{ A}^b$	-	-	0.85	$\Omega$
Forward transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 4.8\text{ A}^b$		4.0	-	-	S
<b>Dynamic</b>							
Drain-source breakdown voltage	$C_{iss}$	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz}$ , see fig. 5		-	1100	-	pF
$V_{DS}$ temperature coefficient	$C_{oss}$			-	170	-	
Gate-source threshold voltage	$C_{rSS}$			-	18	-	
Gate-source leakage	$Q_g$	$V_{GS} = 10\text{ V}$	$I_D = 8.0\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 <sup>b</sup>	-	-	39	nC
Zero gate voltage drain current	$Q_{gs}$			-	-	10	
	$Q_{gd}$			-	-	19	
Drain-source on-state resistance	$t_{d(on)}$	$V_{DD} = 250\text{ V}, I_D = 8.0\text{ A},$ $R_g = 9.1\text{ }\Omega, R_D = 30\text{ }\Omega$ see fig. 10 <sup>b</sup>		-	12	-	ns
Forward transconductance	$t_r$			-	25	-	
Drain-source breakdown voltage	$t_{d(off)}$			-	27	-	
$V_{DS}$ temperature coefficient	$t_f$			-	19	-	
Gate input resistance	$R_g$	$f = 1\text{ MHz}$ , open drain		0.7	-	3.7	$\Omega$
Internal drain inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal source inductance	$L_S$			-	7.5	-	
<b>Drain-Source Body Diode Characteristics</b>							
Continuous source-drain diode current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode		-	-	8.0	A
Pulsed diode forward current <sup>a</sup>	$I_{SM}$			-	-	28	
Body diode voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 8.0\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	2.0	V
Body diode reverse recovery time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 8.0\text{ A},$ $di/dt = 100\text{ A}/\mu\text{s}^b$		-	490	740	ns
Body diode reverse recovery charge	$Q_{rr}$			-	3.0	4.5	$\mu\text{C}$
Forward turn-on time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

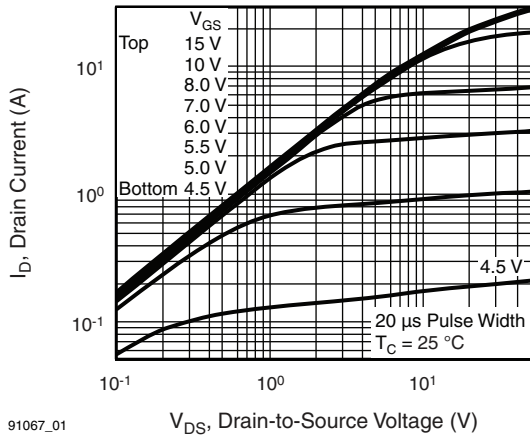


Fig. 1 - Typical Output Characteristics,  $T_C = 25\text{ }^\circ\text{C}$

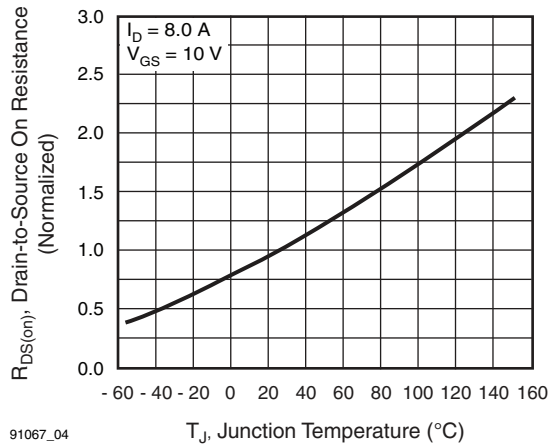


Fig. 4 - Normalized On-Resistance vs. Temperature

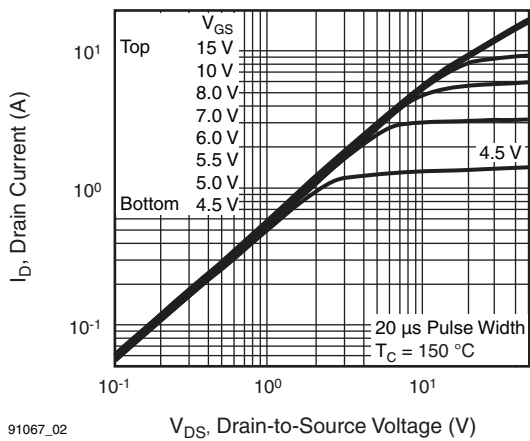


Fig. 2 - Typical Output Characteristics,  $T_C = 150\text{ }^\circ\text{C}$

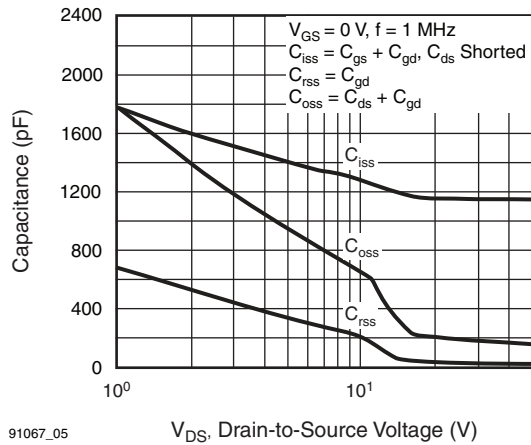


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

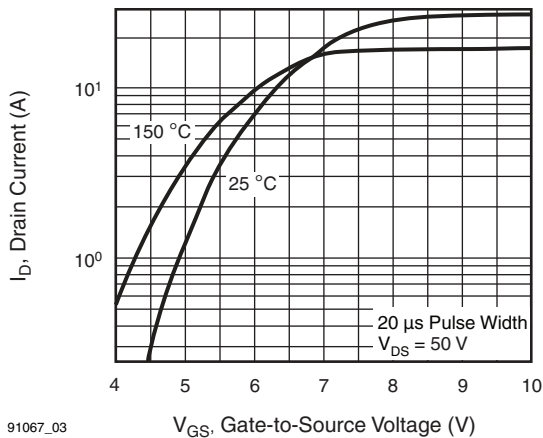


Fig. 3 - Typical Transfer Characteristics

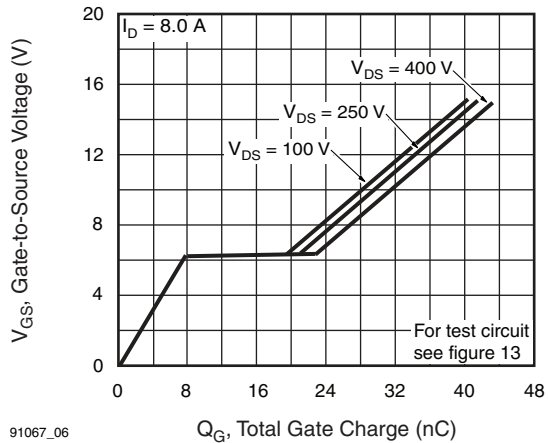
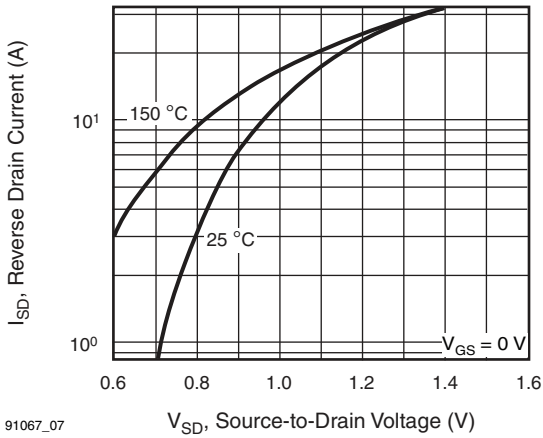
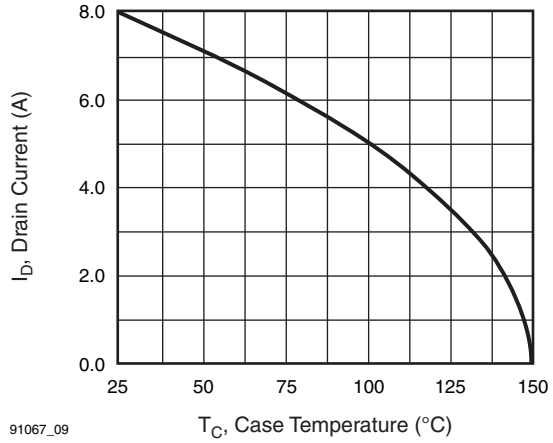


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



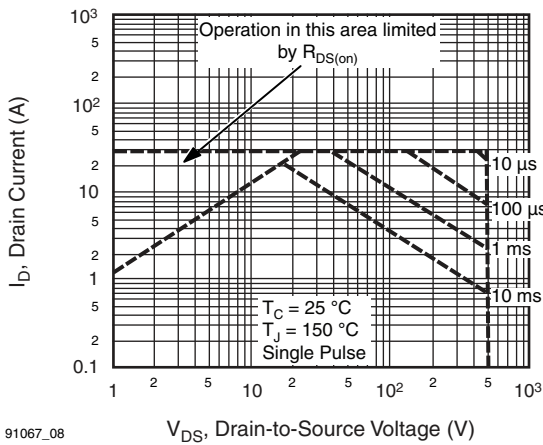
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



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Fig. 9 - Maximum Drain Current vs. Case Temperature



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Fig. 8 - Maximum Safe Operating Area

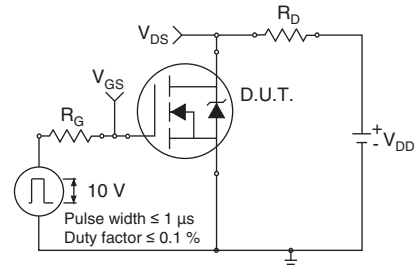


Fig. 10a - Switching Time Test Circuit

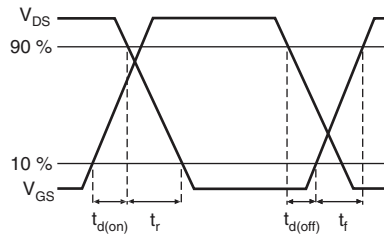
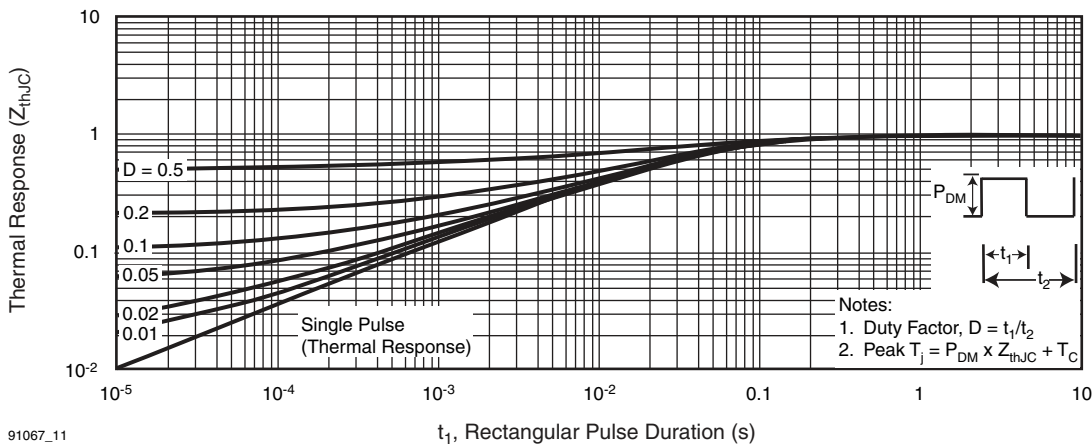


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

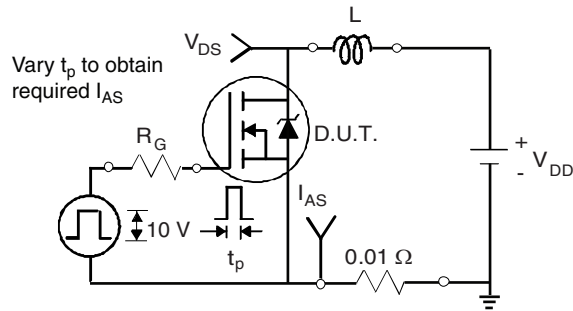


Fig. 12a - Unclamped Inductive Test Circuit

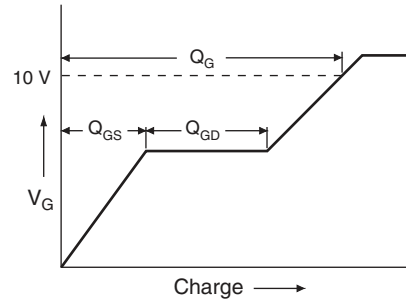


Fig. 13a - Basic Gate Charge Waveform

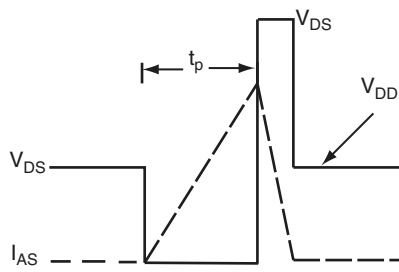


Fig. 12b - Unclamped Inductive Waveforms

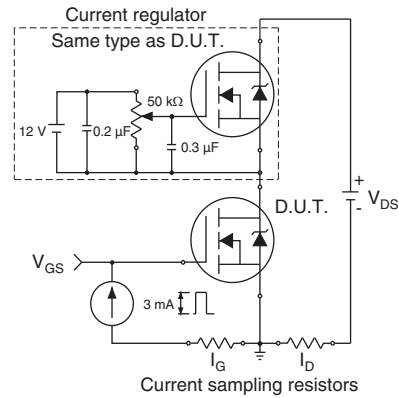
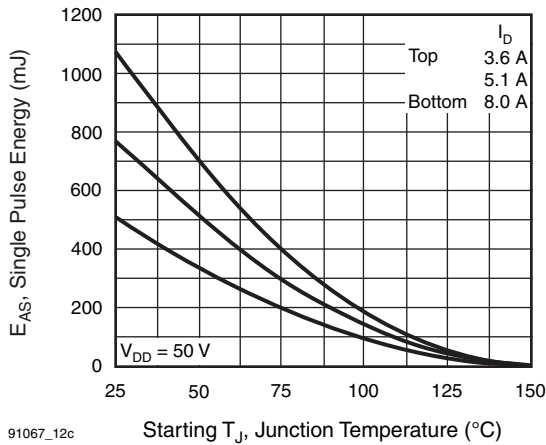
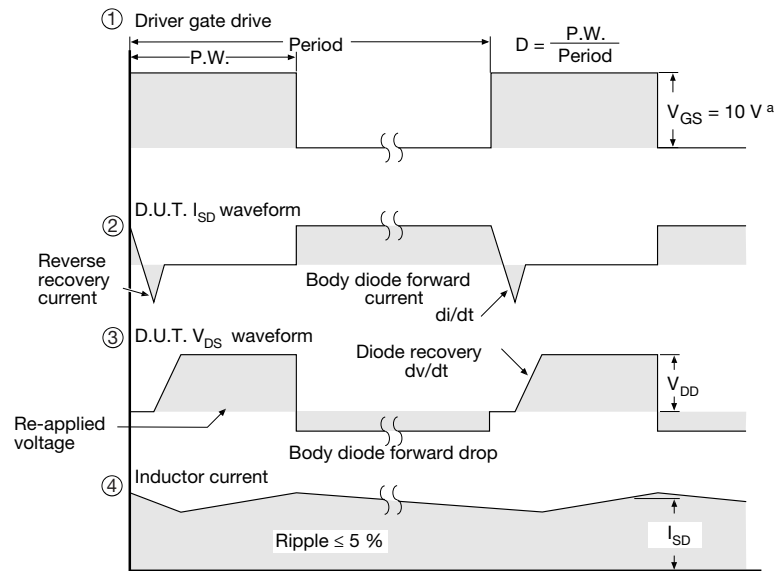
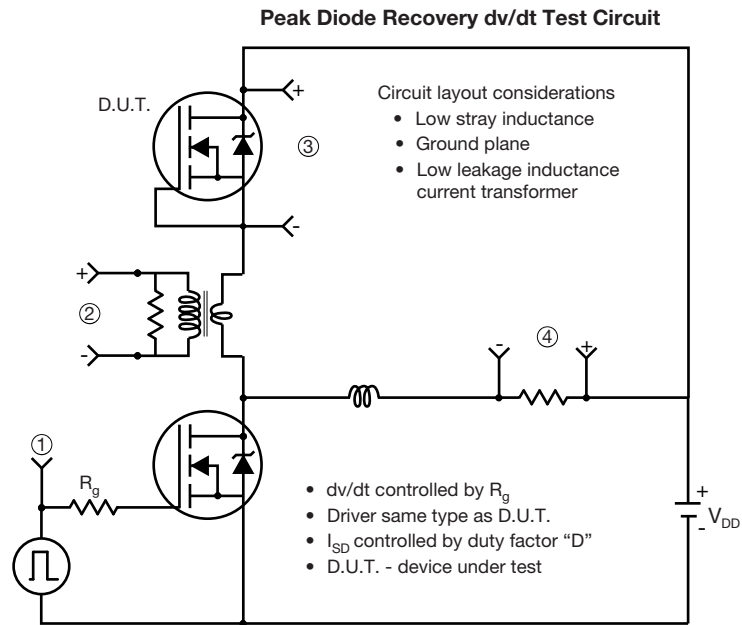


Fig. 13b - Gate Charge Test Circuit



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Fig. 12c - Maximum Avalanche Energy vs. Drain Current



**Note**  
 a.  $V_{GS} = 5 V$  for logic level devices

**Fig. 14 - For N-Channel**

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# TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: E21-0621-Rev. D, 04-Nov-2021  
 DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM



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